2.5 V 1:2 AnyLevel[™] Input to LVDS Fanout Buffer / Translator

The NB6L11S is a differential 1:2 clock or data receiver and will accept AnyLevel™ input signals: LVPECL, CML, LVCMOS, LVTTL, or LVDS. These signals will be translated to LVDS and two identical copies of Clock or Data will be distributed, operating up to 2.0 GHz or 2.5 Gb/s, respectively. As such, the NB6L11S is ideal for SONET, GigE, Fiber Channel, Backplane and other Clock or Data distribution applications.

The NB6L11S has a wide input common mode range from GND + 50 mV to V_{CC} – 50 mV. Combined with the 50 Ω internal termination resistors at the inputs, the NB6L11S is ideal for translating a variety of differential or single–ended Clock or Data signals to 350 mV typical LVDS output levels.

The NB6L11S is the 2.5 V version of the NB6N11S and is offered in a small 3 mm X 3 mm 16–QFN package. Application notes, models, and support documentation are available at www.onsemi.com.

Features

- Input Clock Frequency > 2.0 GHz
- Input Data Rate > 2.5 Gb/s
- RMS Clock Jitter -0.5 ps, Typical
- 622 Mb/s Data Dependent Jitter 6 ps, Typical
- 380 ps Typical Propagation Delay
- 120 ps Typical Rise and Fall Times
- Single Power Supply; $V_{CC} = 2.5 \text{ V} \pm 5\%$
- These are Pb-Free Devices

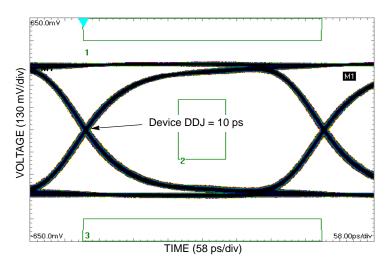


Figure 2. Typical Output Waveform at 2.488 Gb/s with PRBS 2^{23-1} (V_{INPP} = 400 mV; Input Signal DDJ = 14 ps)



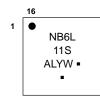
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MARKING DIAGRAM*



QFN-16 MN SUFFIX CASE 485G



A = Assembly Location

L = Wafer Lot Y = Year W = Work Week

= Pb–Free Package

(Note: Microdot may be in either location)
*For additional marking information, refer to
Application Note AND8002/D.

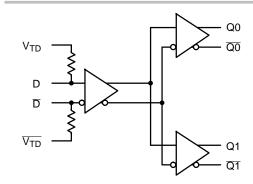


Figure 1. Logic Diagram

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

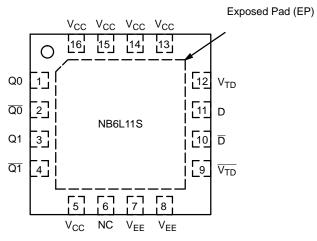


Figure 3. NB6L11S Pinout, 16-pin QFN (Top View)

Table 1. PIN DESCRIPTION

Pin	Name	I/O	Description			
1	Q0	LVDS Output	Non–inverted D output. Typically loaded with 100 Ω receiver termination resistor across differential pair.			
2	Q0	LVDS Output	Inverted D output. Typically loaded with 100 Ω receiver termination resistor across differential pair.			
3	Q1	LVDS Output	Non–inverted D output. Typically loaded with 100 Ω receiver termination resistor across differential pair.			
4	Q1	LVDS Output	Inverted D output. Typically loaded with 100 Ω receiver termination resistor across differential pair.			
5	V _{CC}	-	Positive Supply Voltage.			
6	NC		No Connect.			
7	V _{EE}		Negative Supply Voltage.			
8	V _{EE}		Negative Supply Voltage.			
9	$\overline{V_{TD}}$	-	Internal 50 Ω termination pin for $\overline{\mathbb{D}}$.			
10	D	LVPECL, CML, LVDS, LVCMOS, LVTTL	Inverted Differential Clock/Data Input (Note 1).			
11	D	LVPECL, CML, LVDS, LVCMOS, LVTTL	Non-inverted Differential Clock/Data Input (Note 1).			
12	V_{TD}	-	Internal 50 Ω termination pin for $\overline{D}.$			
13	V _{CC}	-	Positive Supply Voltage.			
14	V _{CC}	-	Positive Supply Voltage.			
15	V _{CC}	-	Positive Supply Voltage.			
16	V _{CC}	-	Positive Supply Voltage.			
EP			Exposed pad. The exposed pad (EP) on the package bottom must be attached to a heat–sinking conduit. The exposed pad may only be electrically connected to V _{EE} .			

In the differential configuration when the input termination pins (V_{TD}, √(TD)) are connected to a common termination voltage or left open, and if no signal is applied on D, D input, then the device will be susceptible to self–oscillation.

Table 2. ATTRIBUTES

Chara	Value			
ESD Protection	Human Body Model Machine Model Charged Device Model	> 2 kV > 200 V > 1 kV		
Moisture Sensitivity (Note 2)	Pb-Free Pkg			
	QFN-16	Level 1		
Flammability Rating Oxygen Inc	dex: 28 to 34	UL 94 V-0 @ 0.125 in		
Transistor Count	225			
Meets or exceeds JEDEC Spec EIA/JESD78 IC Latchup Test				

^{2.} For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

Symbol	Parameter	Condition 1	Condition 2	Rating	Unit
V _{CC}	Positive Power Supply	GND = 0 V		3.8	V
V _{IN}	Positive Input	GND = 0 V	$V_{IN} \le V_{CC}$	3.8	V
I _{IN}	Input Current Through R _T (50 Ω Resistor)	Static Surge		35 70	mA mA
losc	Output Short Circuit Current Line-to-Line (Q to $\overline{\mathbf{Q}}$) Line-to-End (Q or $\overline{\mathbf{Q}}$ to GND)	Q or Q Q to Q to GND	Continuous Continuous	12 24	mA
T _A	Operating Temperature Range	QFN-16		-40 to +85	°C
T _{stg}	Storage Temperature Range			-65 to +150	°C
θ_{JA}	Thermal Resistance (Junction-to-Ambient) (Note 3)	0 lfpm 500 lfpm	QFN-16 QFN-16	41.6 35.2	°C/W
θ _{JC}	Thermal Resistance (Junction-to-Case)	1S2P (Note 3)	QFN-16	4.0	°C/W
T _{sol}	Wave Solder Pb-Free			265	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

3. JEDEC standard multilayer board – 1S2P (1 signal, 2 power) with 8 filled thermal vias under exposed pad.

Table 4. DC CHARACTERISTICS, CLOCK INPUTS, LVDS OUTPUTS V_{CC} = 2.375 V to 2.625 V, GND = 0 V, $T_A = -40^{\circ}C$ to $+85^{\circ}C$

Symbol	Characteristic	Min	Тур	Max	Unit
I _{CC}	Power Supply Current (Note 8)		30	45	mA
DIFFERE	NTIAL INPUTS DRIVEN SINGLE-ENDED (Figures 15, 16, 20, and 22)				
V _{th}	Input Threshold Reference Voltage Range (Note 7)	GND +100		V _{CC} – 100	mV
V _{IH}	Single-ended Input HIGH Voltage	V _{th} + 100		V _{CC}	mV
V _{IL}	Single-ended Input LOW Voltage	GND		V _{th} – 100	mV
DIFFERE	NTIAL INPUTS DRIVEN DIFFERENTIALLY (Figures 11, 12, 13, 14, 21, and 23)				
V _{IHD}	Differential Input HIGH Voltage	100		V _{CC}	mV
V _{ILD}	Differential Input LOW Voltage	GND		V _{CC} – 100	mV
V _{CMR}	Input Common Mode Range (Differential Configuration)	GND + 50		V _{CC} – 50	mV
V _{ID}	Differential Input Voltage (V _{IHD} – V _{ILD})	100		V _{CC} – GND	mV
R _{TIN}	Internal Input Termination Resistor	40	50	60	Ω
LVDS OU	TPUTS (Note 4)				
V _{OD}	Differential Output Voltage	250		450	mV
ΔV_{OD}	Change in Magnitude of V _{OD} for Complementary Output States (Note 9)	0	1	25	mV
Vos	Offset Voltage (Figure 19)	1125		1375	mV
ΔV_{OS}	Change in Magnitude of V _{OS} for Complementary Output States (Note 9)	0	1	25	mV
V _{OH}	Output HIGH Voltage (Note 5)		1425	1600	mV
V _{OL}	Output LOW Voltage (Note 6)	900	1075		mV

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 4. LVDS outputs require 100 Ω receiver termination resistor between differential pair. See Figure 18.

- V_{OH}max = V_{OS}max + ½ V_{OD}max.
 V_{OL}max = V_{OS}min ½ V_{OD}max.
 V_{th} is applied to the complementary input when operating in single–ended mode.
 Iput termination resistor between differential pair. See Figure 10.
 V_{th} is applied to the complementary input when operating in single–ended mode.
 Ipput termination pins open, D/D at the DC level within V_{CMR} and output pins loaded with R_L = 100 Ω across differential.
- 9. Parameter guaranteed by design verification not tested in production.

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Table 5. AC CHARACTERISTICS $V_{CC} = 2.375 \text{ V}$ to 2.625 V, GND = 0 V; (Note 10)

	−40°C			25°C			85°C				
Symbol	Characteristic	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
V _{OUTPP}	Output Voltage Amplitude (@ $V_{INPPmin}$) $f_{in} \le 1.0 \; GHz$ (Figure 4) $f_{in} = 1.5 \; GHz$ $f_{in} = 2.0 \; GHz$	220 200 170	350 300 270		220 200 170	350 300 270		220 200 170	350 300 270		mV
f _{DATA}	Maximum Operating Data Rate	1.5	2.5		1.5	2.5		1.5	2.5		Gb/s
t _{PLH} , t _{PHL}	Differential Input to Differential Output Propagation Delay	250		450	250	380	450	250		450	ps
t _{SKEW}	Duty Cycle Skew (Note 11) Within Device Skew (Note 16) Device—to—Device Skew (Note 15)		8 5 30	45 25 100		8 5 30	45 25 100		8 5 30	45 25 100	ps
t _{JITTER}	RMS Random Clock Jitter (Note 13) $f_{in} = 1.0 \text{ GHz}$ $f_{in} = 1.5 \text{ GHz}$ Peak-to-Peak Data Dependent Jitter (Note 14) $f_{DATA} = 622 \text{ Mb/s}$ $f_{DATA} = 1.5 \text{ Gb/s}$ $f_{DATA} = 2.488 \text{ Gb/s}$		0.5 0.5 6 7 10			0.5 0.5 6 7 10			0.5 0.5 6 7 10		ps
V _{INPP}	Input Voltage Swing/Sensitivity (Differential Configuration) (Note 12)	100		V _{CC} - GND	100		V _{CC} - GND	100		V _{CC} - GND	mV
t _r	Output Rise/Fall Times @ 250 MHz $$ Q, \overline{Q} (20% – 80%)	70	120	170	70	120	170	70	120	170	ps

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm. Electrical parameters are guaranteed only over the declared operating temperature range. Functional operation of the device exceeding these conditions is not implied. Device specification limit values are applied individually under normal operating conditions and not valid simultaneously.

- 11. See Figure 17 differential measurement of t_{skew} = |t_{PLH} t_{PHL}| for a nominal 50% differential clock input waveform @ 250 MHz. 12. Input voltage swing is a single–ended measurement operating in differential mode. 13. RMS jitter with 50% Duty Cycle input clock signal.

- 14. Deterministic jitter with input NRZ data at PRBS 2²³–1 and K28.5.
- 15. Skew is measured between outputs under identical transition @ 250 MHz.
- 16. The worst case condition between $Q0/\overline{Q0}$ and $Q1/\overline{Q1}$ from D, \overline{D} , when both outputs have the same transition.

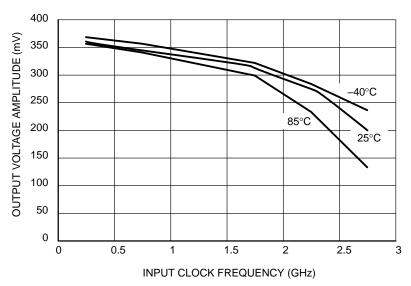


Figure 4. Output Voltage Amplitude (V_{OUTPP}) versus Input Clock Frequency (f_{in}) and Temperature (@ $V_{CC} = 2.5 \text{ V}$)

^{10.} Measured by forcing $V_{INPPmin}$ with 50% duty cycle clock source and V_{CC} – 1400 mV offset. All loading with an external R_L = 100 Ω across "D" and " \overline{D} " of the receiver. Input edge rates 150 ps (20%–80%).

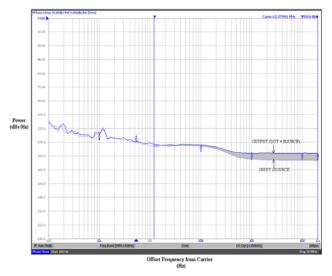


Figure 5. Typical Phase Noise Plot at f_{carrier} = 622.08 MHz

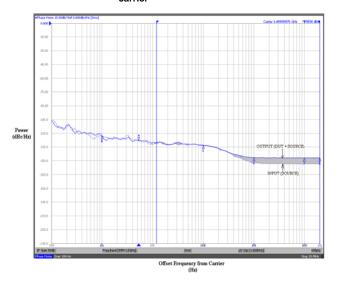


Figure 7. Typical Phase Noise Plot at $f_{carrier} = 1.5 \text{ GHz}$

The above phase noise plots captured using Agilent E5052A show additive phase noise of the NB6L11S device at frequencies 622.08 MHz, 1 GHz, 1.5 GHz and 2 GHz respectively at an operating voltage of 2.5 V in room temperature. The RMS Phase Jitter contributed by the

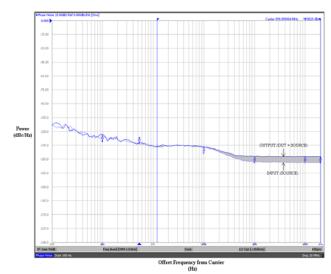


Figure 6. Typical Phase Noise Plot at $f_{carrier} = 1 \text{ GHz}$

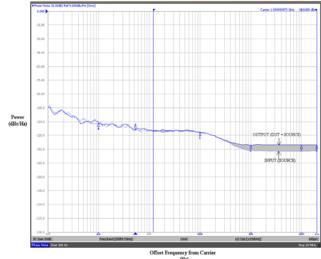


Figure 8. Typical Phase Noise Plot at f_{carrier} = 2 GHz

device (integrated between 12 kHz and 20 MHz; as shown in the shaded region of the plot) at each of the frequencies is 40 fs, 22 fs, 14 fs and 12 fs respectively. The input source used for the phase noise measurements is Agilent E8663B.

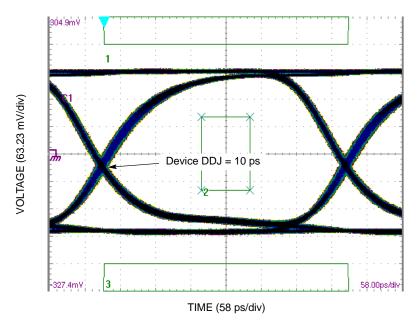


Figure 9. Typical Output Waveform at 2.488 Gb/s with PRBS 2^{23-1} and OC48 mask ($V_{INPP} = 100$ mV; Input Signal DDJ = 14 ps)

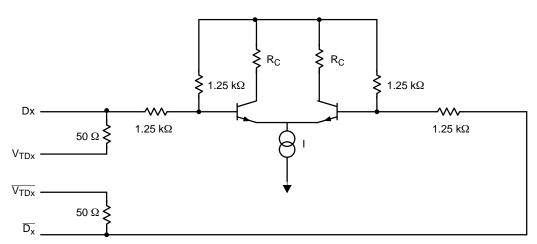


Figure 10. Input Structure

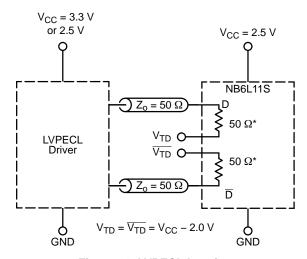


Figure 11. LVPECL Interface

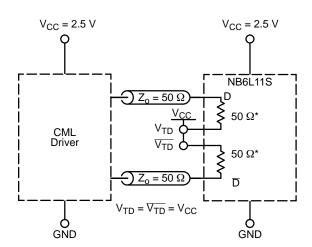
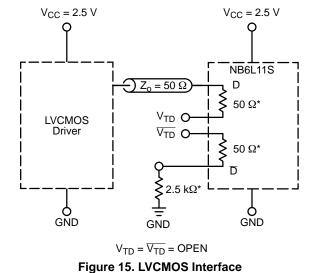


Figure 13. Standard 50 Ω Load CML Interface



*R_{TIN}, Internal Input Termination Resistor.

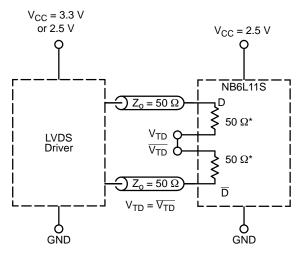


Figure 12. LVDS Interface

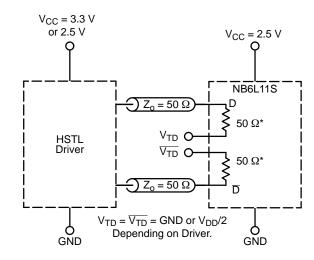


Figure 14. HSTL Interface

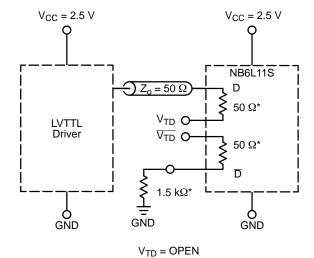


Figure 16. LVTTL Interface

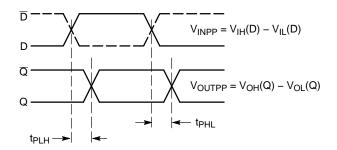


Figure 17. AC Reference Measurement

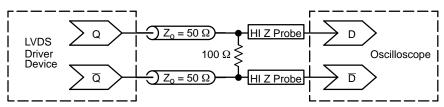


Figure 18. Typical LVDS Termination for Output Driver and Device Evaluation

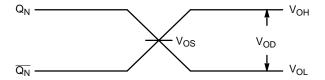


Figure 19. LVDS Output

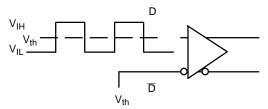


Figure 20. Differential Input Driven Single-Ended

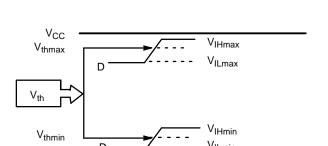


Figure 22. V_{th} Diagram

GND

 V_{ILmin}

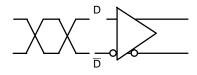


Figure 21. Differential Inputs Driven Differentially

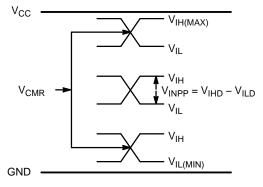


Figure 23. V_{CMR} Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]
NB6L11SMNG	QFN-16, 3 X 3 mm (Pb-Free)	123 Units / Rail
NB6L11SMNR2G	QFN-16, 3 X 3 mm (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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回

TOP VIEW

┅┅

SIDE VIEW

DETAIL B

LEA

A1

PIN ONE

LOCATION

2X 0.10 C

2X 0.10 C

// 0.05 C

□ 0.05 C

NOTE 4





Α

В

SEATING PLANE

C

Ē

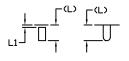
DATE 08 OCT 2021

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS.
 THE TERMINALS.



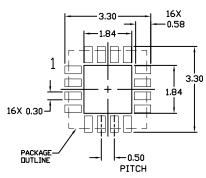
DETAIL B
ALTERNATE
CONSTRUCTIONS

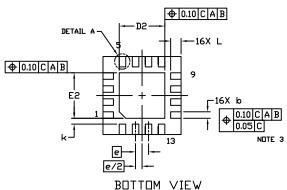


DETAIL A
ALTERNATE TERMINAL
CONSTRUCTIONS

	MILLIME				
DIM	MIN.	N□M.	MAX.		
Α	0.80	0.90	1.00		
A1	0.00	0.03	0.05		
A3		0.20 REF			
b	0.18	0.30			
D	3.00 BSC				
DS	1.65	1.85			
Ε		3.00 BSC	;		
E2	1.65	1.85			
e	0.50 BSC				
k	0.18 TYP				
L	0.30	0.50			
L1	0.00	0.15			

MOUNTING FOOTPRINT





GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code A = Assembly Location

L = Wafer Lot
Y = Year
W = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	QFN16 3X3, 0.5P		PAGE 1 OF 1				

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ZL40203LDG1 ZL40200LDG1 ZL40205LDG1 9FG1200DF-1LF 9FG1001BGLF ZL40202LDG1 PI49FCT20802QE SL2305SC-1T
NB7L1008MNG NB7L14MN1G PI49FCT20807QE PI6C4931502-04LIEX ZL80002QAB1 PI6C4931504-04LIEX PI6C10806BLEX
ZL40226LDG1 8T73S208B-01NLGI SY75578LMG PI49FCT32805QEX PL133-27GC-R CDCV304PWG4 MC10LVEP11DG
MC10EP11DTG MC100LVEP11DG MC100E111FNG MC100EP11DTG NB6N11SMNG NB7L14MMNG NB6L11MMNG
NB6L14MMNR2G NB6L611MNG PL123-02NGI-R NB3N111KMNR4G ADCLK944BCPZ-R7 ZL40217LDG1 NB7LQ572MNG
HMC940LC4BTR ADCLK946BCPZ-REEL7 ADCLK946BCPZ ADCLK854BCPZ ADCLK905BCPZ-R2 ADCLK905BCPZ-R7
ADCLK905BCPZ-WP